L Number			DB	Time stamp
T	2	("6168991").PN.	USPAT;	2002/07/12 13:0
			US-PGPUB;	2002/07/12 13:0
			EPO; JPO;	
			DERWENT;	1
2	2	("6211005").PN.	IBM_TDB	
	_	(0211005).FN.	USPĀT;	2002/07/12 14:0
			US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
•	}		IBM TDB	ĺ
3	0	1 Carron nears cultustell liears (indiim	USPĀT;	2000 (07 (10 1 1
		oxide or ito)").PN.	1	2002/07/12 14:0
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
4	41	adhogion nonna homest	IBM_TDB	
	1		USPAT;	2002/07/12 14:0
		oxide or ito)	US-PGPUB;	1 7 7 7 7 2 2 1110
			EPO; JPO;	ļ
			DERWENT;	
5	0	adhesion near3 tungsten near3 (indium adj	IBM_TDB	
		oxide or ito)	USPAT;	2002/07/12 14:1
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM TDB	
6	0	The state of the s	USPAT;	2002/07/10 11
		oxide or ito)		2002/07/12 14:1
		,	US-PGPUB;	ĺ
	}		EPO; JPO;	
			DERWENT;	
!	0	adhanias	IBM TDB	
		adhesi\$2 near6 tungsten near6 (indium adj	USPAT;	2002/07/12 14:1
	1	oxide or ito)	US-PGPUB;	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
	ļ		EPO; JPO;	
			DERWENT;	
				1
1	i ol	tungsten near3 (plug or contact) near6	IBM_TDB	
	l	(indium add oxide on its) and i	USPAT;	2002/07/12 14:1
	i	(indium adj oxide or ito) and dram.ti,ab.	US-PGPUB;	
	}		EPO; JPO;	
			DERWENT;	
			IBM TDB	
ĺ	2	tungsten near3 (indium adj oxide or ito)	USPAT:	2002/07/12 15:44
		and dram.ti,ab.	US-PGPUB;	2002/01/12 15:44
	1		EDO: TDO	
	ļ		EPO; JPO;	
İ			DERWENT;	
0	2	tungsten near6 /indian - 44	IBM_TDB	
1	-	tungsten near6 (indium adj oxide or ito)	USPAT;	2002/07/12 15:45
ļ	,	and dram.ti,ab.	US-PGPUB;	
ļ			EPO; JPO;	1
1			DERWENT;	
	1		IBM TDB	
_	2	tungsten near12 (indium adj oxide or ito)		2000 (57 (5)
1		and dram.ti,ab.	USPAT;	2002/07/12 15:45
			US-PGPUB;]
[ĺ		EPO; JPO;	
Í	1		DERWENT;	
	404	humanitan and 10 at an	IBM TDB	
	494	tungsten near12 (indium adj oxide or ito)	USPAT;	2002/07/12 15:46
			US-PGPUB;	2002/01/12 15:46
İ	1		EPO; JPO;	
1	1			
			DERWENT;	
]	1	tungsten norm12 /imain	IBM_TDB	
	† .	tungsten near12 (indium adj oxide or ito)	USPĀT;	2002/07/12 15:47
İ	[]	near12 (adhere or adhesion)	US-PGPUB;	
-	ļ		EPO; JPO;	
			DERWENT;	
	İ			
		tungsten near12 (indium adj oxide or ito)	IBM_TDB	
	1 1		HODAM	2000/07/10 15 00
	1 1	near12 (adhere or all	USPAT;	2002/07/12 16:03
	1 1	near12 (adhere or adhesion or adhesive)	US-PGPUB;	2002/07/12 16:03
	1 1	near12 (adhere or adhesion or adhesive)	US-PGPUB;	2002/07/12 16:03
	1 1	near12 (adhere or adhesion or adhesive)		2002/07/12 16:03

15	1	(w or tungsten) near12 (indium adj oxide or ito) near12 (adhere or adhesion or	USPAT; US-PGPUB;	2002/07/12 16:23
		adhesive)	EPO; JPO; DERWENT;	
16	21	(w or tungsten) near12 (prevent or	IBM_TDB	
1 0	21	preventing) near12 oxidation near12	USPAT;	2002/07/12 16:36
		(contact or plug)	US-PGPUB; EPO; JPO;	
		(concast of prag)	DERWENT;	
	Í		IBM TDB	
17	1	(prevent or preventing) near12 oxidation	USPĀT;	2002/07/12 16:49
		near12 indium adj oxide	US-PGPUB;	2002,01,12 10.43
			EPO; JPO;	
			DERWENT;	
18	7	/hamhalama and and a day	IBM_TDB	
10	/	(tantalum adj nitride or tan) near12 (tungsten or w) near12 (indium adj oxide	USPAT;	2002/07/12 16:53
		or ito or indium adj tin adj oxide	US-PGPUB;	1
		or ros or maram day cin day oxide,	EPO; JPO; DERWENT;	
			IBM TDB	
19	530	(USPAT;	2002/07/12 16:53
1	İ	(tungsten or w) near12 (barrier or	US-PGPUB;	
1		passivation)	EPO; JPO;	
			DERWENT;	
20	53	(tantalum adj nitride or tan) near3	IBM_TDB	0000/07/10 10 1
		(tungsten or w) near3 (barrier or	USPAT; US-PGPUB;	2002/07/12 16:54
		passivation)	EPO; JPO;	
		•	DERWENT;	ļ
			IBM TDB	
21	5	(tantalum adj nitride or tan) near3	USPĀT;	2002/07/12 16:58
		(tungsten or w) near3 (barrier or	US-PGPUB;	
		passivation).ti,ab.	EPO; JPO;	
			DERWENT;	
22	135	(tantalum adj nitride or tan) near3	IBM_TDB USPAT;	2002/07/12 17:18
		(tungsten or w).ti,ab.	US-PGPUB;	2002/07/12 17:18
		-	EPO; JPO;	
			DERWENT;	
23	8	/hambalam all all the	IBM_TDB	
23	0	<pre>(tantalum adj nitride or tan) near3 (tungsten or w).ti.</pre>	USPAT;	2002/07/12 17:26
		(cangaten of w).ti.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	1
24	277	(tantalum adj nitride or tan) near3	USPAT;	2002/07/12 17:27
		(tungsten or w) near12 barrier	US-PGPUB;	
]			EPO; JPO;	
			DERWENT;	
25	18	(tantalum adj nitride or tan) near3	IBM_TDB	2002/07/10 10 15
		(tungsten or w) near12 barrier.ti,ab.	USPAT; US-PGPUB;	2002/07/12 19:16
		January and and and and and and and and and and	EPO; JPO;	
			DERWENT;	
100			IBM TDB	
26	0	(tantalum adj nitride or tan) near3	USPAT;	2002/07/12 18:08
		(indium adj2 oxide or ito) near12	US-PGPUB;	
]	barrier.ti,ab.	EPO; JPO;	
1			DERWENT;	
27	2	("6265260").PN.	IBM_TDB USPAT;	2002/07/12 19:17
			US-PGPUB;	2002/01/12 19:1/
			EPO; JPO;	
			DERWENT;	
28		/BC1 C0 001 B) - 707	IBM_TDB	
20	2	("6168991").PN.	USPAT;	2002/07/12 19:39
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	

29	C	<pre>("oxidation adj potential near12 (tungsten or W)").PN.</pre>	USPAT; US-PGPUB;	2002/07/12 19:3
			EPO; JPO;	
			DERWENT;	
30		And Anna San San San San San San San San San	IBM TDB	
	55	oxidation adj potential near12 (tungsten or W)	USPAT;	2002/07/12 19:4
		OI W)	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
-	6085	((257/68) or (257/71) or (257/296) or	IBM_TDB	
		(45/300) or $(257/306)$ or $(257/308)$ or	USPAT; US-PGPUB;	2002/07/12 12:5
		(257/309) or $(257/310)$ or $(257/311)$ or	EPO; JPO;	
	ł	1(45)/(61) or $(257/763)$ or $(361/303)$ or	DEDUTE	
		(301/305) or $(361/306.1)$ or $(361/306.3)$ or	IBM TDB	
_	23	(361/311)).CCLS.	_	
	23	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or	USPAT;	2001/08/23 08:4
		("257/308") or ("257/309") or ("257/310")	US-PGPUB;	
		10° ("25//311") or ("257/761") or	EPO; JPO;	
		("257/763") or $("361/303")$ or $("361/305")$	DERWENT; IBM TDB	
		10^{11} ("361/306.1") or ("361/306.3") or	TDM_IDB	
		("361/311")).CCLS.) and semiconductor and		
	1	Capacitor and (tantalum adi oxide or		
	1	tantalum adj pentoxide) and tantalum adj		
	0	nitride and tungsten and substrate 6285072.pn.		
		0200072.pii.	JPO;	2001/08/22 18:20
	3	((("257/68") or ("257/71") or ("257/296")	DERWENT	
		of ("45//300") or ("257/306") or	USPAT; US-PGPUB;	2001/08/22 20:49
	ĺ	("257/308") or ("257/309") or ("257/310")	EPO; JPO;	
		or ("25//311") or ("257/761") or	DERWENT;	
		("257/763") or ("361/303") or ("361/305")	IBM TDB	
		or ("361/306.1") or ("361/306.3") or	_	
	1	("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or		
	[[tantalum adj pentoxide) and indium adj		
		oxide and tungsten and substrate		
	2	((("257/68") or ("257/71") or ("257/296")	USPAT;	2001/00/02 00 10
		or ("257/300") or ("257/306") or	US-PGPUB;	2001/08/23 08:49
	}	("257/308") or $("257/309")$ or $("257/310")$	EPO; JPO;	
		or $("257/311")$ or $("257/761")$ or	DERWENT;	
		("257/763") or ("361/303") or ("361/305")	IBM_TDB	
		or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and	_	
		capacitor and (tantalum adj oxide or	•	
		tantalum adj pentoxide) and indium adj		
1	1	Oxide and tungsten and substrate and		
ĺ	ļ	tantalum adj nitride		
	0	semiconductor and capacitor and (tantalum	EPO; JPO;	2001/08/23 08:47
		ad oxide or tantalum add pentoxide) and	IBM TDB	2001/06/23 08:4/
ļ		tantalum adj nitride and tungsten and		
		substrate		
	١		USPAT;	2001/08/23 08:48
İ	1:		US-PGPUB;	
1	1:	Plibot water and	EPO; JPO;	
			DERWENT; IBM TDB	
	0 s	pemiliconductor and capacitor and (tantalism)	EPO; JPO;	2001/08/23 08:48
	•	d oxide or tantalum adi pentovide) and	DERWENT;	2001/00/23 08:48
	-	indium ad] Oxide and tungsten and	IBM TDB	
		substrate and tantalum adj nitride	[

-		2 ((("257/68") or ("257/71") or ("257/296")	IISDAT.	1 2001 /00 /02 00 5
		or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310")	HC DCDHD	2001/08/23 08:5
		or ("25//311") or ("257/761") or ("257/763") or ("361/303") or ("361/305")	DEDMENT	
		or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and	-	
		capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj		
		oxide and substrate and tantalum adj		
-	(semiconductor and capacitor and (tantalum		2001/08/23 08:50
		adj oxide or tantalum adj pentoxide) and indium adj oxide and substrate and	IBM_TDB	
_		tantalum adj nitride semiconductor and (capacitor or dram) and	EPO; JPO;	2001/08/23 08:51
		pentoxide) and indium adj oxide and	IBM_TDB	2001700723 08:31
_	C	tantalum adj nitride (tantalum adj nitride with work adj	II C D A M	0001/00/0
		function) and semiconductor and dram and capacitor	USPAT; US-PGPUB;	2001/08/23 10:38
			EPO; JPO; DERWENT;	
-	1	(tantalum adj nitride with work adj	IBM_TDB USPAT;	2001/08/23 10:40
		function) and semiconductor and capacitor	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
_	12	(tantalum adj nitride with work adj function) and (257/\$5.ccls. or	USPĀT;	2001/08/23 10:41
		438/\$5.ccls.)	US-PGPUB; EPO; JPO;	
_	3	4663559.pn.	DERWENT; IBM_TDB	
		1003337.pm.	USPAT; US-PGPUB;	2001/08/23 11:16
			EPO; JPO; DERWENT;	
_	0	barrier with tantal\$2 adj nitride with ev	IBM_TDB USPAT;	2001/00/02 11 15
j		3	US-PGPUB;	2001/08/23 11:47
			EPO; JPO; DERWENT;	
-	522	barrier with tantal\$2 adj nitride	IBM_TDB USPAT;	2001/08/23 11:47
			US-PGPUB; EPO; JPO;	
_	1 4 1	dies	DERWENT; IBM TDB	
	141	diffusion adj barrier with tantal\$2 adj nitride	USPAT; US-PGPUB;	2001/08/23 11:47
			EPO; JPO; DERWENT;	
-	0	diffusion adj barrier with tantal\$2 adj	IBM_TDB	
		nitride with work adj function	USPAT; US-PGPUB;	2001/08/23 11:48
			EPO; JPO; DERWENT;	
	0	diffusion adj barrier with tantal\$2 adj	IBM_TDB USPAT;	2001/08/23 11:48
		nitride same work adj function	US-PGPUB; EPO; JPO;	, 00, 20 11.40
			DERWENT;	
	0	(diffusion adj barrier with tantal\$2 adj nitride) same work adj function	IBM_TDB USPAT;	2001/08/23 11:48
		and restriction	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	

-		(diffusion adj barrier with tant\$4 adj	USPAT;	2001/08/23 11:49
ł		nitride) same work adj function	US-PGPUB;	2001/08/23 11:49
-		_	EPO; JPO;	
			DERWENT;	
		(diffusion add barrior with torted and	IBM TDB	
	-	- I (analog dat parties with lanesa and	USPAT;	2001/08/23 12:06
		nitride) and (tant\$4 adj nitride same work adj function)		
		adj Idilectolly	EPO; JPO;	
			DERWENT; IBM TDB	1
-	c	diffusion adj barrier with tant\$4 adj	USPAT;	2001/00/02 10 06
		nitride with indium adj oxide	US-PGPUB;	2001/08/23 12:06
		_	EPO; JPO;	
	İ		DERWENT;	
_	3	(diffusion add barrier with tantia add	IBM_TDB	
		(diffusion adj barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and	USPAT;	2001/08/23 12:38
		capacitor.ti,ab.)	US-PGPUB;	
	1	Supuction.cr, ab.)	EPO; JPO;	
	1		DERWENT; IBM TDB	
	1	1 (-44,44) ad t current with fam 54 and	USPAT;	2001/00/22 10 40
		nitride) and (semiconductor tilab and	US-PGPUB;	2001/08/23 12:42
		capacitor.ti,ab.)	EPO; JPO;	
			DERWENT;	
,	17	(hammian with a said of said o	IBM TDB	
	1	(barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and	USPAT;	2001/08/23 12:52
	1	capacitor.ti,ab.)	US-PGPUB;	
		cupacitor.cr, ab.)	EPO; JPO;	
	-		DERWENT;	
	2	jp-10320569\$-\$.did.	IBM_TDB JPO;	2001 (00 (00 1
			DERWENT	2001/08/23 19:32
	626	effective adj refractive adj index	JPO;	2001/08/23 19:33
			DERWENT	2001/00/23 19:33
	99	ad refractive ad index near()	JPO;	2001/08/23 19:33
	61	mode	DERWENT	
	01	effective adj refractive adj index near4 mode	JPO;	2001/08/23 19:34
	310	effective adj refractive adj index near4	DERWENT	
ļ		mode	USPAT; US-PGPUB;	2001/08/23 19:34
			EPO;	
ĺ			DERWENT;	
	0.0		IBM TDB	
	26		USPAT;	2001/08/23 19:34
		waveguide adj mode	US-PGPUB;	= 101,00,20 13.34
			EPO;	1
ļ	ľ		DERWENT;	
	6349	((257/68) or (257/71) or (257/296) or	IBM_TDB	
		(257/300) or (257/306) or (257/308) or	USPAT;	2001/12/10 13:36
		(257/309) or (257/310) or (257/311) or	US-PGPUB;	
1		(257/761) or $(257/763)$ or $(361/303)$ or	EPO; JPO; DERWENT;	
		(361/305) or $(361/306.1)$ or $(361/306.3)$ or	IBM TDB	
1		(361/311)).CCLS.	100	1
1	0	("L4 and (indium adj2 oxide near10	USPAT;	2001/12/10 13:39
1	1	(storage or first or second or cell) adj2	US-PGPUB;	
4	1	electrode))").PN.	EPO; JPO;	
	}		DERWENT;	
	1	((("257/68") or ("257/71") or ("257/296")	IBM_TDB	
	-		USPAT;	2001/12/10 13:43
		("257/308") or $("257/309")$ or $("257/310")$	US-PGPUB;	
1		or ("257/311") or ("257/761") or	EPO; JPO; DERWENT;	
	ĺ	("257/763") or $("361/303")$ or $("361/305")$	IBM TDB	
	1	or ("361/306.1") or ("361/306.3") or		
	i	("361/311")).CCLS.) and (indium adi2 oxide		
}	1	nearlU (storage or first or second or		
1	,	cell) adj2 electrode)		i e

-	or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxid same (storage or first or second or cell) adj2 electrode)	DERWENT; IBM_TDB	
-	("257/761") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CLS.) and (indium adj2 oxid same (storage or first or second or cell) adj2 electrode)	EPO; JPO; DERWENT; IBM_TDB	
-	("25///63") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxid same (storage or first or second or cell) adj2 electrode)	IBM_TDB	
-	("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxid same (storage or first or second or cell)		
-	same (storage or first or second or cell)	e	
-	adj2 electrode)	e	
-	dula electrode)	- 1	ĺ
-	0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		
	9 ((("257/68") or ("257/71") or ("257/296")	II.C.D.T.	
	104 (237/300") or ("257/306") or	USPAT;	2001/12/10 14:5
	(257/308) or $(257/309)$ or $(257/3109)$	US-PGPUB; EPO; JPO;	
	10^{-1} ($207/311^{-1}$) or ("257/761") or	DERWENT;	
ĺ	("257/763") or ("361/303") or ("361/305")	IBM_TDB	i
	Or (301/300,1") or ("361/306 3") on	_	
	(301/311")), CCLS.) and (indium add and)		
_	Same electrode) and capacitor ti ab		
1	- 1 () (= 0) (O) (D) (Z) () (I) (O) (I) (O)	USPAT;	2001/12/10 15:17
1	or ("257/300") or ("257/306") or	US-PGPUB;	2001/12/10 15:1/
	("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or	EPO; JPO;	
ļ	("257/763") or ("361/305") or ("361/305")	DERWENT;	
	or ("361/306.1") or ("361/305") or ("361/305")	IBM_TDB	
1	("361/311")).CCLS.) and (purpose same		
ſ	indium adj oxide same electrode) and		
	Capacitor.ti.ab.		
•	$2 \mid ((("257/68") \text{ or } ("257/71") \text{ or } ("257/206")$		
	10± (23//300") or ("257/306") or	USPAT;	2001/12/10 15:06
	("25//308") or $("257/309")$ or $("257/3109")$	US-PGPUB;	
1	101 (237/311") or ("257/761") or	EPO; JPO; DERWENT;	
	("25//763") or $("361/303")$ or $("361/305")$	IBM TDB	
ĺ	$101 \times 301/300.1$ ") or ("361/306 3") or	IBM_IDB	1
	(301/311")).CCLS.) and (nurnose same		
	Indian ad Oxide same electrode)		1
	- \\\ 23//00 Of ("Z3/// ") or ("257/20cm)	USPAT;	2001/12/10 15:10
	101 (23//300") or ("257/306") or	US-PGPUB;	2001/12/10 15:10
[("257/308") or ("257/309") or ("257/310")	EPO; JPO;	
	or ("257/311") or ("257/761") or	DERWENT;	
	("257/763") or ("361/303") or ("361/305")	IBM TDB	
	or ("361/306.1") or ("361/306.3") or ("361/311"))	_	1
}	("361/311")).CCLS.) and ((tungsten or w)]
1	near4 (plug or via)) and (electrode same indium adj oxide) and (dielectric near10		
	(tantalum adj oxide or tantalum adj		
	pencoxide)) and (capacitor or dram)+:		
1	0 ((("257/68") or ("257/71") or ("257/296")	1	
	01 (23//300") or ("257/306") or	USPAT;	2001/12/10 15:13
	("25//308") or $("257/309")$ or $/"257/310"$	US-PGPUB;	
	1 0 1 2 3 1 3 1 1 1 0r ("757 / 761 ")	EPO; JPO;	
1	("25//63") or $("361/303")$ or $("361/305")$	DERWENT;	
1	1 0 - 1 0 0 - 1 0 0 0 1 1 0 0 1 1 1 0 0 0 0	IBM_TDB	
	(301/311")).CCLS.) and ((tungston on)		
ł	Heart (Prug or Via)) and (electrode come		
1	Indian ad Oxide and ((insulating an		
	Insulator or dielectric) near10 /tantal	1	
1	adjustice of tantalim adj pentovido.		
	Capacitor of Gram or electrode 1: -1		
1	\circ (((257/08") or ("257/71") or ("257/206")	USPAT;	2001/12/10 15:14
1	1 0 1 (201/ 300) OF ("25//306") or	US-PGPUB;	2001/12/10 15:14
	$(^{2}3//308")$ or $(^{2}57/309")$ or $(^{2}57/310")$	EPO; JPO;	
Ì	V= \ 23//311") or \(\"\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	DERWENT;	
1	("257/763") or ("361/303") or ("361/305")	IBM TDB	
	101 (301/300.1") or ("361/306 3") on		
1	("361/311")).CCLS.) and ((tungsten or w)		
	meaty (plug or Via)) and (alactrode and	1	
1	indium adj oxide) and ((insulating or insulator or dielectric) nearly (
	insulator or dielectric) near10 (tantalum adj oxide or tantalum adj pentoxide))		

		0 ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
-		near12 (plug or via)) and (clungsten or w) near12 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same		2001/12/10 15:36
_		indium adj oxide) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) nearl2 (tantalum adj oxide or tantalum adj pentoxide)) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
-	0	("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/12/10 15:17
-	0	or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or	IBM_TDB USPAT; US-PGPUB;	2001/12/10 15:37
		("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((reductive or prtoection or protecting or protect) same tantalum adj nitride same indium adj oxide)	EPO; JPO; DERWENT; IBM_TDB	
	0	oxide) same (protect or protection or protecting or protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/12/10 15:39
	0	(tantalum adj nitride same indium adj oxide) same (protect or protection or protecting or protection)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/12/10 15:40
	33	tantalum adj nitride same indium adj oxide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:40

<u> </u>	0	tantalum add add the		
		tantalum adj nitride same indium adj oxide same (protect or cover or reduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/12/10 15:41
-	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:42
_	1815	("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near12 indium oxide) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	1815	("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near4 indium oxide) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	1	("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near2 indium oxide) ((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	1	and (electrode near2 indium adj oxide) hdp near3 silicon adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 10:16